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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Atty. Ref.:

Examiner:

Group:

1035-501

2811

In re Patent Application of

TAKAFUJI et al

Serial No.

10/802,735

Filed:

March 18, 2004

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For: SEMICONDUCTOR DEVICE AND METHOD OF

MANUFACTURING THE SAME

consideration in this US National Phase Application.

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Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

## INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of							
the Patent and Trademark Office the references listed on the attached form PTO-1449.							
All listed documents are attached.							
This application was filed after June 30, 2003 so that copies of U.S. Patent							
Publications are not required and are not attached.							
☐ Listed foreign patent publications and other documents are enclosed.							
The partial translations were provided to the undersigned by the applicants'							
foreign representative. The undersigned has no knowledge regarding the pertinency of							
the partially translated portions vis-á-vis the document as a whole. The partial							
translations are merely provided for whatever convenience they may be.							
The listed documents were cited in the ISR and copies should have been							
supplied by WIPO directly to the US PTO. If copies are not timely received from WIPO,							

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

please telephone the undersigned so that copies can be timely supplied for the Examiner's

## TAKAFUJI et al Serial No. 10/802,735

The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted, NIXON & VANDERHYE P.C.

June 7, 2004

HWB:lsh

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H. Warren Burnam, Jr. Reg. No. 29,366

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INFORMATION DISCLOSURE CITATION				DOCKET NO.	SERIAL NO.			
			1035		10/802,735			
(Use several sheets if necessary)				TAKAFUJI et al				
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\*Examiner Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include

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Matsumoto et al, "70 nm SOI-CMOS of 135 GHz  $f_{\text{max}}$  with Dual Offset-Implanted Source-Drain Extension Structure for RF/Analog and Logic Applications", International Electron Device Meeting, December 2001, pp.

copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)